

Si, Ge, Si-Ge, and GaAs Thin Films on Flexible Metallic Substrates for Fabrication of Thin-Film Solar Cells

Disclosure Number

201002469

Technology Summary

This is improvement to the invention disclosure # 201002395. We have optimized the process conditions to grow STO and gamma-Al₂O₃ layers using pulsed laser deposition and demonstrated the growth of epitaxial Si and made a device.

Inventor

PARANTHAMAN, MARIAPPAN

Chemical Sciences Division

Licensing Contact

REEVES, MARK E

UT-Battelle, LLC

Oak Ridge National Laboratory

Rm 145, Bldg 4500N, MS: 6196

1 Bethel Valley Road

Oak Ridge, TN 37831

Office Phone: (865) 576-2577

E-mail: REEVESME@ORNL.GOV

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